

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chang, et al. Attorney Docket: TSM-476RI
Patent No.: 6,346,476 B1 Patent Issued: 02/12/2002
Reissue Filed: Herewith
Title: Method for Enhancing Line-to-Line Capacitance Uniformity of Plasma
Enhanced Chemical Vapor Deposited (PECVD) Inter-Metal Dielectric (IMD)
Layers

Mail Stop: REISSUE
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Dear Sir:

Prior to examination on the merits, Applicants respectfully submit the amendments and remarks set forth below.

In the claims:

Please add the following new claims:

26. (new) A method for forming a dielectric layer, comprising:

providing a substrate;

forming over the substrate, while employing a plasma enhanced chemical vapor

deposition (PECVD), a silicon containing dielectric layer, wherein

when forming the silicon containing dielectric layer there is controlled a temperature of

the substrate by use of pressure of a backside cooling gas.